

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Richard A. Blanchard

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Serial No.: 10/724,849

MAY 09 2005

Filed: December 1, 2003

Title: High Voltage Power MOSFET Having A Voltage Sustaining Region That  
Includes Doped Columns Formed By Trench Etching and Ion Implantation

Art Unit: 2811

Examiner: Steven Ho Yin Loke

Docket No.: GS 156 D1

Customer No.: 27774

Confirmation No. 2167

Via Facsimile 703-872-9306  
 Commissioner for Patents  
 PO Box 1450  
 Alexandria, VA 22313-1450

AMENDMENT

Sir:

In response to the (*Ex parte Quayle*) Office Action dated February 28, 2005, kindly the above-identified application as follows. In addition, any deficiencies may be charged to deposit account No. 50-1047.

05/24/2005 LWISE1 0000002 501047 10724849

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Certificate of Facsimile Transmission

I hereby certify that this document and any document referenced herein has been transmitted via facsimile to the US Patent and Trademark Office at (703) 872-9306 on May 8, 2005.

Karin L. Williams, Reg. No. 36,721

(Printed Name of Person Mailing Correspondence)

Karin L. Williams  
(Signature)